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	Application No.	Applicant(s)	
Notice of Allowability	10/733,216	TU ET AL.	
	Examiner	Art Unit	
	Tu-Tu Ho	2818	:
The MAILING DATE of this communication at All claims being allowable, PROSECUTION ON THE MERITS herewith (or previously mailed), a Notice of Allowance (PTOL NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATEN of the Office or upon petition by the applicant. See 37 CFR 1	S IS (OR REMAINS) CLOSED -85) or other appropriate comm T RIGHTS. This application is	in this application. If not inclunumication will be mailed in du	ided ie course. THIS
1. $igtimes$ This communication is responsive to <u>Papers filed 12/1</u>	<u>1/2003</u> .		
2. ☑ The allowed claim(s) is/are <u>1-21</u> .			
3. $igotimes$ The drawings filed on <u>11 December 2003</u> are accepted	d by the Examiner.		
4. Acknowledgment is made of a claim for foreign priori a) All b) Some* c) None of the: 1. Certified copies of the priority documents 2. Certified copies of the priority documents 3. Copies of the certified copies of the priorit International Bureau (PCT Rule 17.2(a)). * Certified copies not received: Applicant has THREE MONTHS FROM THE "MAILING DA noted below. Failure to timely comply will result in ABANDO THIS THREE-MONTH PERIOD IS NOT EXTENDABLE. 5. A SUBSTITUTE OATH OR DECLARATION must be s INFORMAL PATENT APPLICATION (PTO-152) which 6. CORRECTED DRAWINGS (as "replacement sheets") (a) including changes required by the Notice of Drafts 1) hereto or 2) to Paper No./Mail Date (b) including changes required by the attached Exam Paper No./Mail Date Identifying Indicia such as the application number (see 37 C each sheet. Replacement sheet(s) should be labeled as such attached Examiner's comment regarding REQUIREMENT.	have been received. have been received in Applicately documents have been received. TE" of this communication to find DNMENT of this application. ubmitted. Note the attached Exercises reason(s) why the oather gives reason(s) why the oather gives reason's Patent Drawing Review. TET 1.84(c)) should be written on in the header according to 37 Ceposit of BIOLOGICAL MATERIAL PROCEIVANT TO THE PROCESS TO THE P	ion No ed in this national stage application and in this national stage application that is a reply complying with the recommendation and the drawings in the front (not to the drawings in the front (not to the drawings in the submitted). TERIAL must be submitted	requirements NOTICE OF
Attachment(s) 1. ☑ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-9 3. ☑ Information Disclosure Statements (PTO-1449 or PTO/Paper No./Mail Date 01/29/2004 4. ☐ Examiner's Comment Regarding Requirement for Depo	48) 6. Interview Paper No SB/08), 7. Examiner	nformal Patent Application (P Summary (PTO-413), ./Mail Date s Amendment/Comment s Statement of Reasons for A 	,
	David Malma		
	Dávíd Nelms Supervisory Patent Examiner Technology Center 2800		

U.S. Patent and Trademark Office PTOL-37 (Rev. 1-04)

DETAILED ACTION

Allowable Subject Matter

1. Claims 1-21 are allowable over the prior art of record.

The following is an examiner's statement of reasons for allowance: The prior art of record fails to teach or render obvious a memory cell and a method of manufacturing thereof having all exclusive limitations as recited in claims 1, 7, and 8, comprising a capacitor having two electrodes, a lining over the capacitor, a spacer, and a gate electrode extending over the capacitor, characterized in either that:

the spacer has a first non-planer profile configured to engage a second non-planar profile comprising ends of one of the electrodes and the lining, the electrodes are vertically disposed electrodes, the lining is insulating, and the spacer isolates an end of the one of the electrodes from an extension of the gate electrode or the gate electrode couples to the capacitor; or that:

the electrodes are formed in an opening in a substrate, ends of one of the electrodes extend over and are parallel to the substrate, the spacer isolates one end of the one of the electrodes from an extension of the gate electrode, and the spacer includes a protrusion conforming to a recess defined by and end of the lining ends and the one end of the one of the electrodes.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue

fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

- 2. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Copies of the references are not being furnished with this Office Action per MPEP § 707.05(a).
- a) U.S. Patent 6,661,050 to Tzeng et al. discloses a 1T-1C memory cell having a trench capacitor and a transistor planar with the capacitor.
- b) U.S. Patent 5,950, 084 to Chao discloses a DRAM cell having a dual-packed trench capacitor and a transistor planar with the capacitor.
- 3. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Tu-Tu Ho whose telephone number is (571) 272-1778. The examiner can normally be reached on 6:30 am 5:00 pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, DAVID NELMS can be reached on (571) 272-1787. The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR

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system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Tu-Tu Ho

September 04, 2004

David Nelms
Supervisory Patent Examiner

Technology Center 2800